

113CNQ100SL-L

Technical Data Data Sheet N2332, Rev.-

RoHS 🗭

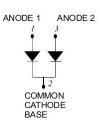
113CNQ100SL-L SCHOTTKY RECTIFIER



Features

- 175℃ T_J operation
- Center tap module
- Very Low forward voltage drop
- High purity, high temperature epoxy encapsulation for enhanced mechanical strength and moisture resistance
- High frequency operation
- Guard ring for enhanced ruggedness and long term reliability
- Baseplate and Terminals finish: Pure Sn plated
- Low profile, high current package
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional electrical and life testing can be performed upon request

Circuit Diagram



Applications

- Switching power supply
- Converters
- Free-Wheeling diodes
- Reverse battery protection

Maximum Ratings:

Characteristics	Symbol	Condition	Max.	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	-	100	V
Average Rectified Forward Current	I _{F (AV)}	50% duty cycle @T _c =95°C, rectangular wave form	55(Per Leg) 110(Per Device)	A
Peak One Cycle Non-Repetitive Surge Current (per leg)	I _{FSM}	10 ms, half Sine pulse	720	А
Non-Repetitive Avalanche Energy(peg leg)	E _{AS}	T _J =25℃, I _{AS} =1A, L=30mH	15	mJ
Repetitive Avalanche Current(peg leg)	I _{AR}	Current decaying linearly to zero in 1 μ sec Frequency limited by T _J max. V _A =1.5×V _R typical	1	A

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Electrical Characteristics:

Characteristics	Symbol	Condition	Тур.	Max.	Units
Forward Voltage Drop (Per leg) *	V _{F1}	@ 55A, Pulse, T _J = 25 °C @110A, Pulse, T _J = 25 °C	-	0.81 1.00	V
	V _{F2}	@ 55A, Pulse, TJ = 125 °C @ 110A, Pulse, TJ = 125 °C	-	0.66 0.79	V
Reverse Current (Per leg) *	I _{R1}	$@V_R = rated VR T_J = 25 °C$	0.01	1	mA
	I _{R2}	$@V_R = rated VR T_J = 125 °C$	1.8	32	mA
Junction Capacitance (Per leg)	Ст	@V _R = 5V, T _C = 25 °C f _{SIG} = 1MHz	1180	1960	pF

* Pulse width < 300 µs, duty cycle < 2%

Thermal-Mechanical Specifications:

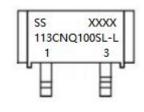
Characteristics	Symbol	Condition	Specification	Units
Junction Temperature	TJ	-	-55 to +175	°C
Storage Temperature	T _{stg}	-	-55 to +175	°C
Typical Thermal Resistance Junction to Case (per leg)	R _{θJC}	DC operation	0.50	°C/W
Typical Thermal Resistance Junction to Case (per package)	R _{θJC}	DC operation	0.25	°C/W
Typical Thermal Resistance, case to Heat Sink	$R_{ hetacs}$	Mounting surface, smooth and greased	0.30	°C/W
Mounting Torque	ТМ	-	40(min)	Kalam
			58(max)	Kg-cm
Approximate Weight	wt	-	7.8	g
Case Style	PRM2-SL			

Ordering Information

Device	Package	Shipping
113CNQ100SL-L	PRM2-SL	100pcs / box

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXX is YYWW

1st row SS YYWWL 2nd row 113CNQ100SL-L 3rd row 1 3 (pin) SS = SS YY = Year WW = Week

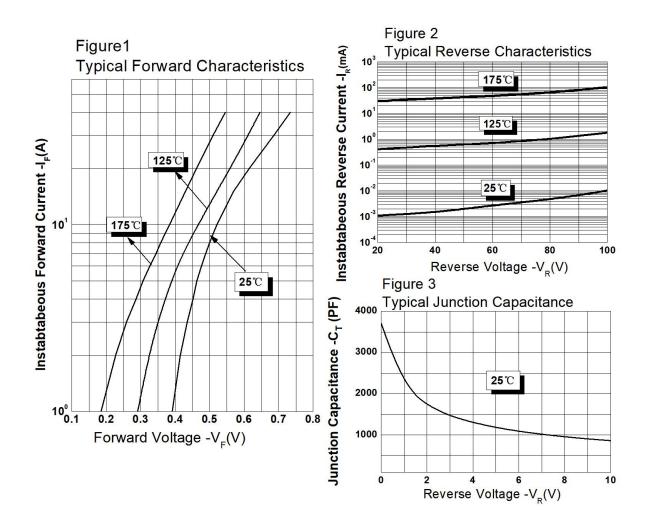
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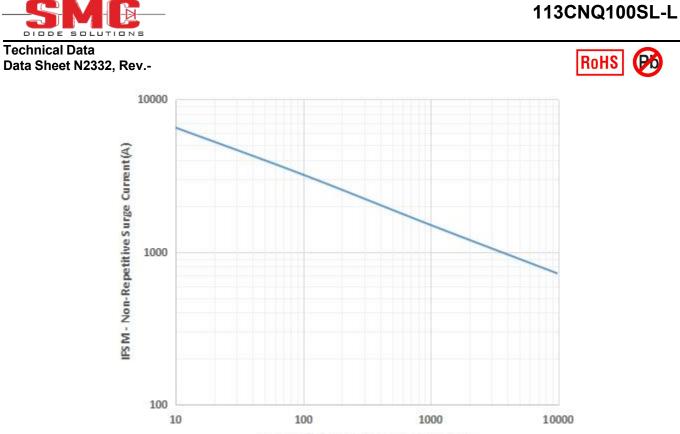
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Ratings and Characteristics Curves

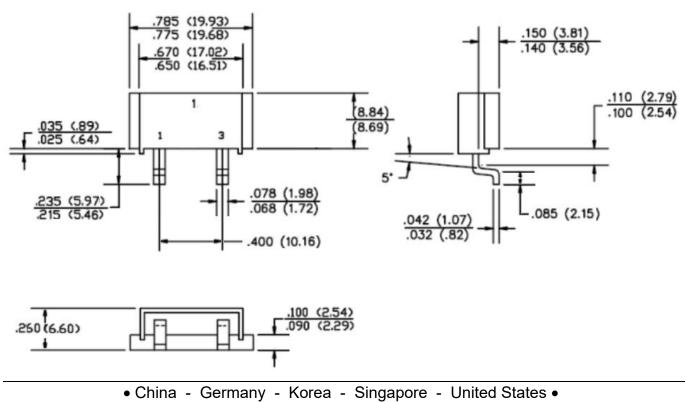




Tp - Half Sine Wave Pulse Duration(us)

Mechanical Dimensions PRM2-SL (Inches/Millimeters)

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